

1 IN THE CLAIMS:

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3 Please amend claim 1 as follows:

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5 1. (Amended) A method [for] of using Si-Ge-C in selective etch applications [in
6 conjunction with a silicon substrate], comprising:7 growing one or more epitaxial layers [sequentially, starting at the silicon
8 substrate, wherein at least one of the epitaxial layers comprises Si-Ge-C, wherein the
9 carbon of the Si-Ge-C layer is about 4.5 atomic percent] on a single crystal silicon
10 substrate, at least one of which is a Si-Ge-C layer, wherein the carbon of the Si-Ge-C
11 layer is an amount sufficient to exhibit etch selectivity with respect to the single crystal
12 silicon substrate and/or one or more of the epitaxial layers adjacent the Si-Ge-C layer,
13 and14 [selectively etching the one or more layers adjacent to the Si-Ge-C layer and/or
15 the Si-Ge-C layer wherein the selective etching includes applying a KOH etchant to the
16 Si-Ge-C layer] etching the Si-Ge-C layer, and the single crystal silicon substrate and/or
17 one or more of the epitaxial layers adjacent the Si-Ge-C layer.

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19 Please add claims 2-20 as follows:

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21 ^{49.}
22 ~~2.~~ The method of claim 1, wherein the Si-Ge-C layer etches slower than the
one or more adjacent epitaxial layers.

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24 ^{50.}
25 ~~3.~~ The method of claim 1, wherein the Si-Ge-C layer etches slower than the
single crystal silicon substrate.

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27 ^{51.}
28 ~~4.~~ The method of claim 1, wherein the Si-Ge-C layer etches faster than the one
or more adjacent epitaxial layers.

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30 ^{52.}
~~5.~~ The method of claim 1, wherein the Si-Ge-C layer etches faster than the
single crystal silicon substrate.

1 ^{53,}
2 ~~6.~~ The method of claim 1, wherein the etching includes applying an etchant
3 selected from the group of KOH and HNA.

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5 ⁵⁴
6 ~~7.~~ A method of using Si-Ge-C in selective etch applications in conjunction with a
7 single crystal substrate, comprising:

8 growing one or more epitaxial layers sequentially, starting at the single crystal
9 substrate surface, wherein at least one of the epitaxial layers comprises Si-Ge-C,
10 wherein the carbon of the Si-Ge-C layer is up to 5 atomic percent; and
11 etching the Si-Ge-C layer, and the single crystal substrate and/or one or more of
the epitaxial layers adjacent the Si-Ge-C layer.

12 ^{55,} ⁵⁴
13 ~~8.~~ The method of claim ~~7~~, wherein the Si-Ge-C layer etches slower than the one
14 or more adjacent epitaxial layers.

15 ^{56,} ⁵⁴
16 ~~9.~~ The method of claim ~~7~~, wherein the Si-Ge-C layer etches slower than the
17 single crystal substrate.

18 ^{57,} ⁵⁴
19 ~~10.~~ The method of claim ~~7~~, wherein the Si-Ge-C layer etches faster than the one
20 or more adjacent epitaxial layers.

21 ^{58,} ⁵⁴
22 ~~11.~~ The method of claim ~~7~~, wherein the Si-Ge-C layer etches faster than the
23 single crystal substrate.

24 ^{59,} ^{54 55 56 57 58}
25 ~~12.~~ The method of claim ~~7, 8, 9, 10, or 11~~, wherein the single crystal substrate is
26 a material selected from the group of silicon, silicon-germanium, and germanium.

27 ^{60,} ⁵⁴
28 ~~13.~~ The method of claim ~~7~~, wherein the etching includes applying an etchant
29 selected from the group of KOH and HNA.
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61.

61. 14. A method of using Si-Ge-C in selective etch applications in conjunction with a substrate, comprising:

growing one or more layers sequentially, starting at the substrate, wherein at least one of the layers comprises Si-Ge-C, wherein the carbon of the Si-Ge-C layer is up to 10 atomic percent, and etching the Si-Ge-C layer and one or more layers adjacent to the Si-Ge-C layer and/or the substrate.

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61. 15. The method of claim *61* 14, wherein the Si-Ge-C layer etches slower than the one or more adjacent layers.

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61. 16. The method of claim *61* 14, wherein the Si-Ge-C layer etches slower than the substrate.

64.

61. 17. The method of claim *61* 14, wherein the Si-Ge-C layer etches faster than the one or more adjacent layers.

65.

61. 18. The method of claim *61* 14, wherein the Si-Ge-C layer etches faster than the substrate.

66.

61 62 63 64 65 19. The method of claim *61 62 63 64 65* 14, 15, 16, 17, or 18, wherein the substrate is a material selected from the group of silicon, silicon-germanium, and germanium.

67.

61 20. The method of claim *61* 14, wherein the etching includes applying an etchant selected from the group of KOH and HNA.--

1 Please enter claim 1 in clean form as follows:

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3 *Sub 2.1*
4 1. A method of using Si-Ge-C in selective etch applications, comprising:
5 growing one or more epitaxial layers on a single crystal silicon substrate, at least
6 one of which is a Si-Ge-C layer, wherein the carbon of the Si-Ge-C layer is an amount
7 sufficient to exhibit etch selectivity with respect to the single crystal silicon substrate
8 and/or one or more of the epitaxial layers adjacent to the Si-Ge-C layer; and
9 etching the Si-Ge-C layer, and the single crystal silicon substrate and/or one or
10 more of the epitaxial layers adjacent to the Si-Ge-C layer.
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